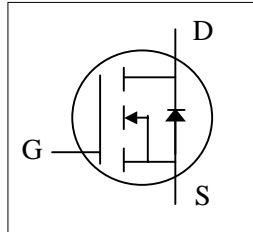


AP4002H/J**RoHS-compliant Product****Advanced Power
Electronics Corp.***N-CHANNEL ENHANCEMENT MODE**POWER MOSFET*

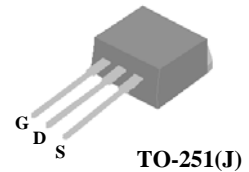
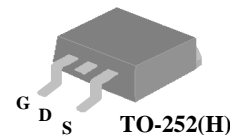
- ▼ 100% Avalanche Test
- ▼ Fast Switching Characteristics
- ▼ Simple Drive Requirement



BV_{DSS}	600V
$R_{DS(ON)}$	5 Ω
I_D	2A

Description

AP4002 series are specially designed as chopper regulator, DC/DC converter and power drive application. The APEC MOSFET provide the best combination of fast switching, ruggedized design and cost-effectiveness.

**TO-251(J)****TO-252(H)**

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2	A
I_{DM}	Pulsed Drain Current ¹	8	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	20	W
	Linear Derating Factor	0.16	W/ $^\circ C$
E_{AS}	Single Pulse Avalanche Energy ²	20	mJ
I_{AR}	Avalanche Current	2	A
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	6.25	$^\circ C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	$^\circ C/W$


Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	600	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=1.0A$	-	-	5	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=2.0A$	-	1.5	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=600V, V_{GS}=0V$	-	-	100	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 30V$	-	-	± 1	μA
Q_g	Total Gate Charge ³	$I_D=2A$	-	12	19	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=480V$	-	2	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	5.5	-	nC
$t_{d(on)}$	Turn-on Delay Time ³	$V_{DD}=200V$	-	10	-	ns
t_r	Rise Time	$I_D=1A$	-	12	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=50\Omega, V_{GS}=10V$	-	52	-	ns
t_f	Fall Time	$R_D=200\Omega$	-	19	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	375	600	pF
C_{oss}	Output Capacitance	$V_{DS}=10V$	-	170	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	45	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ³	$T_j=25^\circ\text{C}, I_S=2A, V_{GS}=0V$	-	-	1.5	V
t_{rr}	Reverse Recovery Time ³	$I_S=2A, V_{GS}=0V,$	-	340	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	2.2	-	μC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Starting $T_j=25^\circ\text{C}$, $V_{DD}=50V$, $L=10mH$, $R_G=25\Omega$
3. Pulse test

THIS PRODUCT IS ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR USE IN CONSUMER APPLICATIONS. APPLICATIONS OR USE IN LIFE SUPPORT OR OTHER SIMILAR MISSION-CRITICAL DEVICES OR SYSTEMS ARE NOT AUTHORIZED.

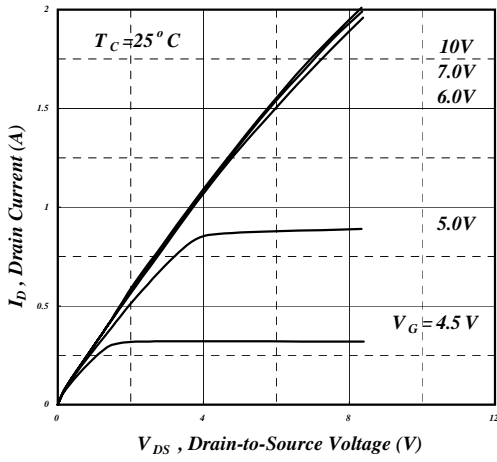


Fig 1. Typical Output Characteristics

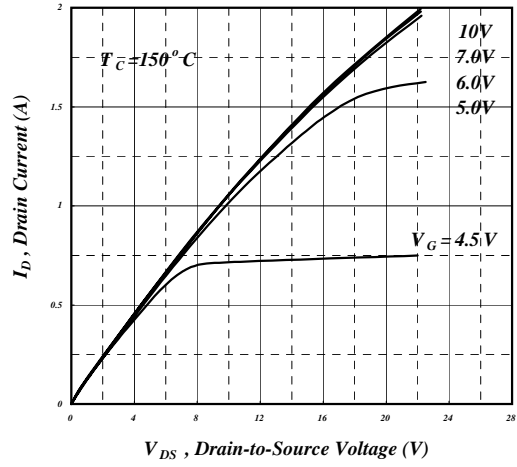


Fig 2. Typical Output Characteristics

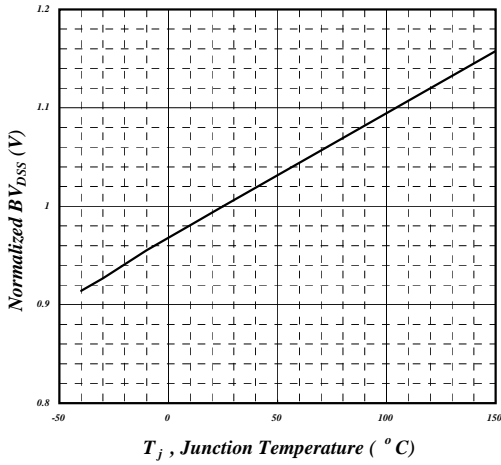


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

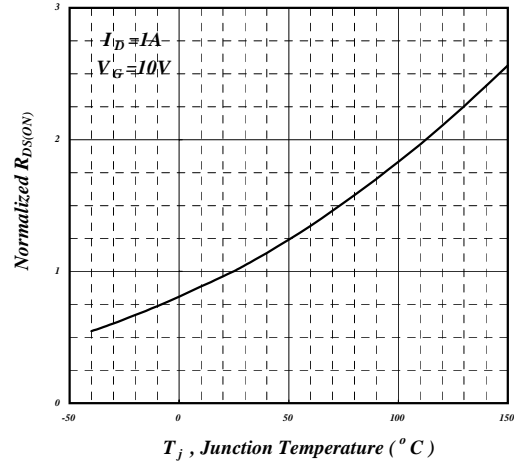


Fig 4. Normalized On-Resistance v.s. Junction Temperature

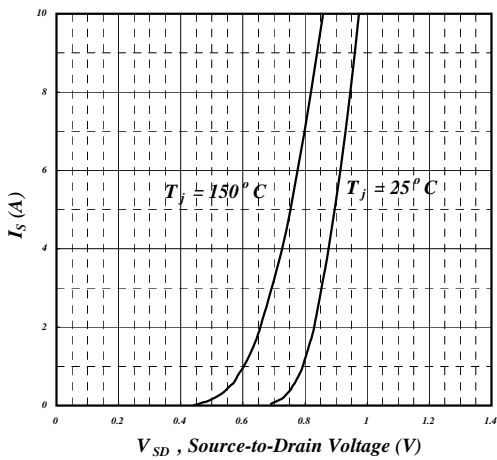


Fig 5. Forward Characteristic of Reverse Diode

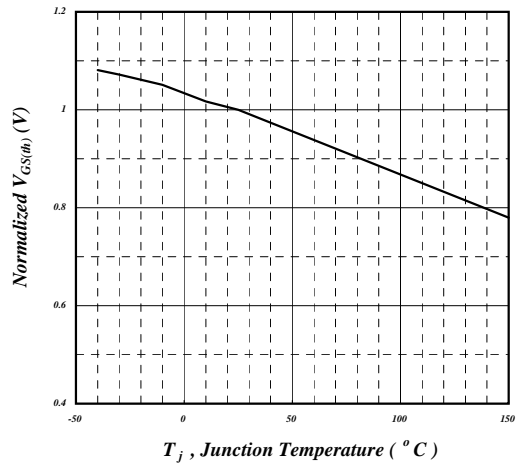


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

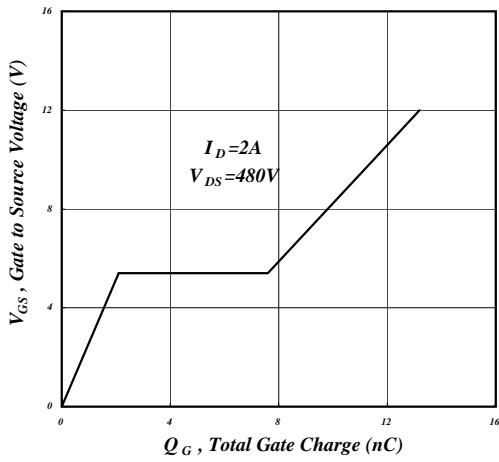


Fig 7. Gate Charge Characteristics

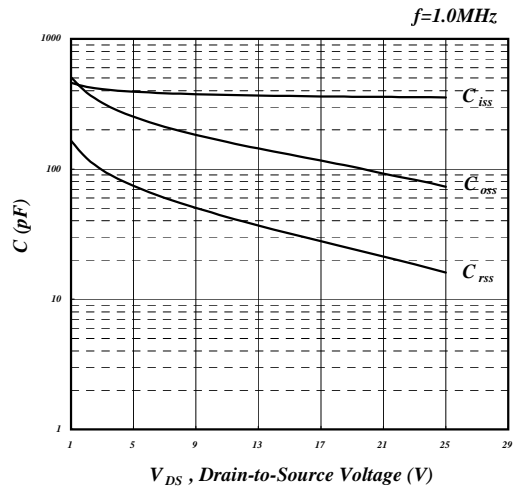


Fig 8. Typical Capacitance Characteristics

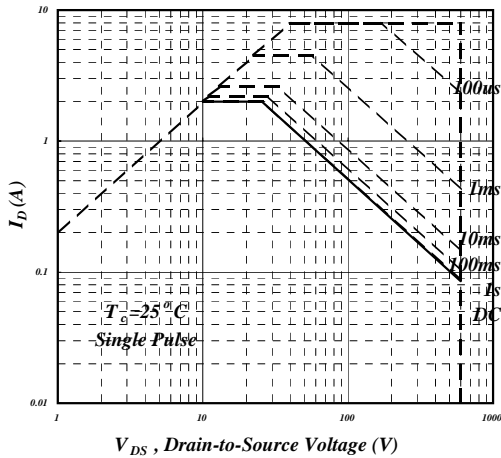


Fig 9. Maximum Safe Operating Area

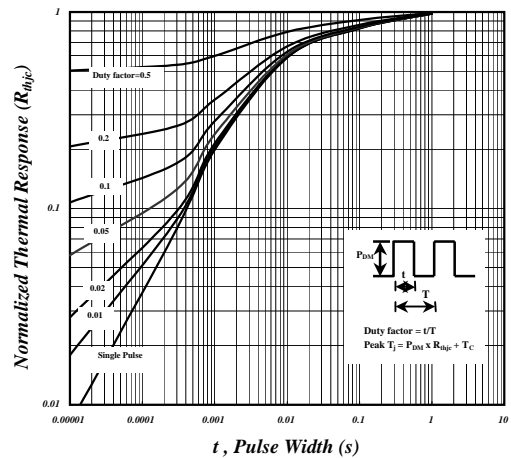


Fig 10. Effective Transient Thermal Impedance

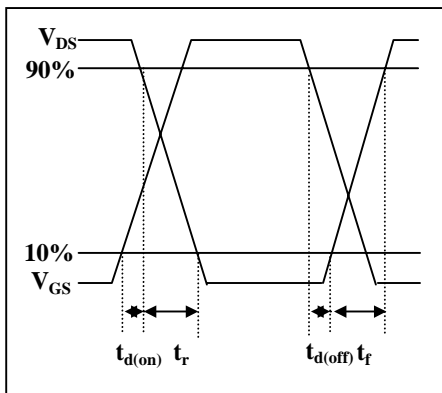


Fig 11. Switching Time Waveform

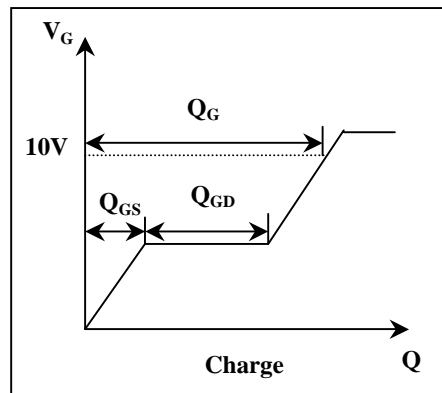
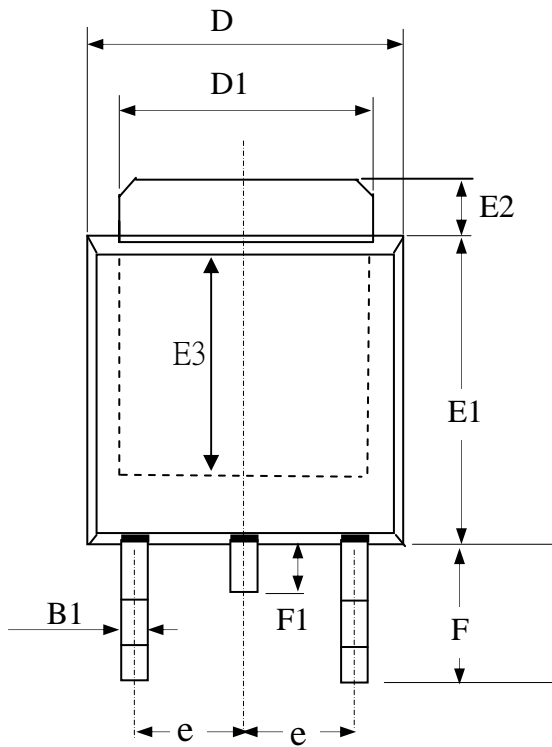


Fig 12. Gate Charge Waveform

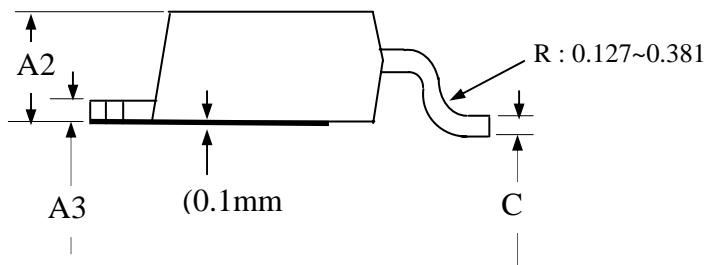


Package Outline : TO-252

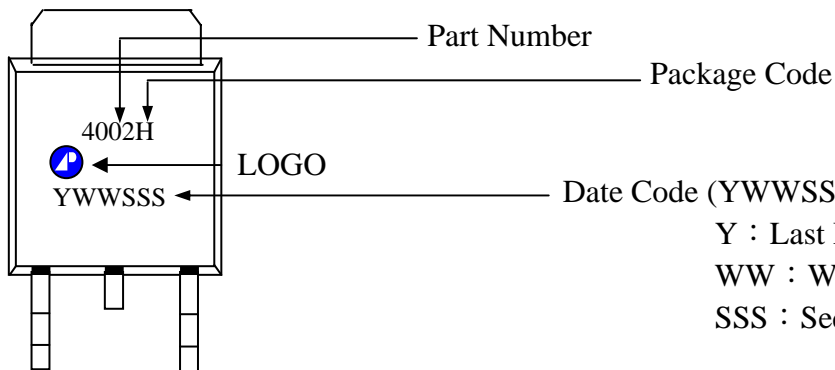


SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.5	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

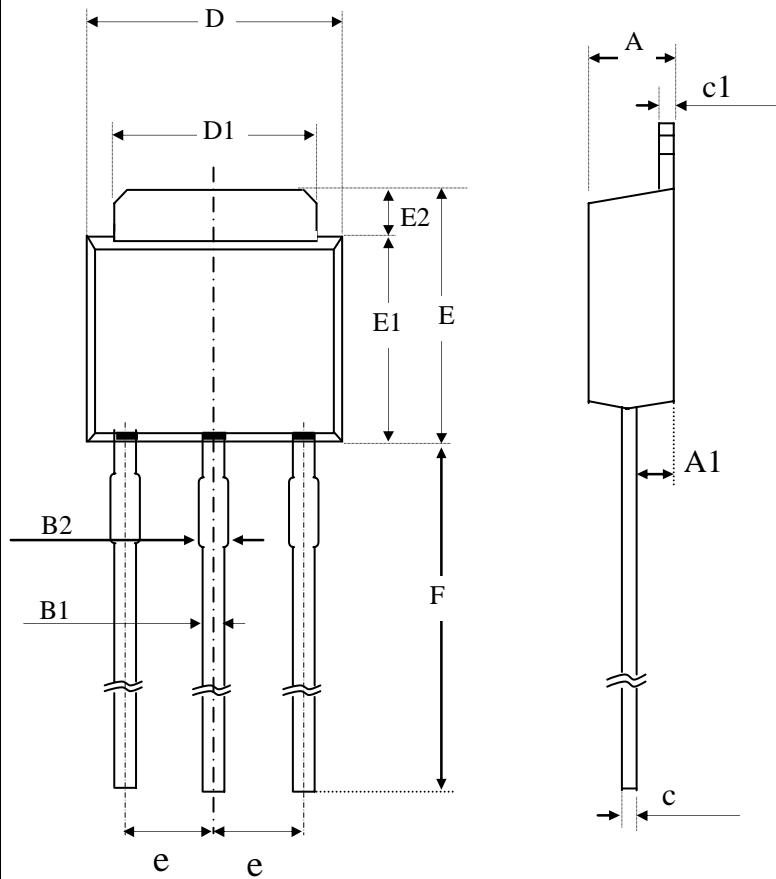
- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.



Part Marking Information & Packing : TO-252



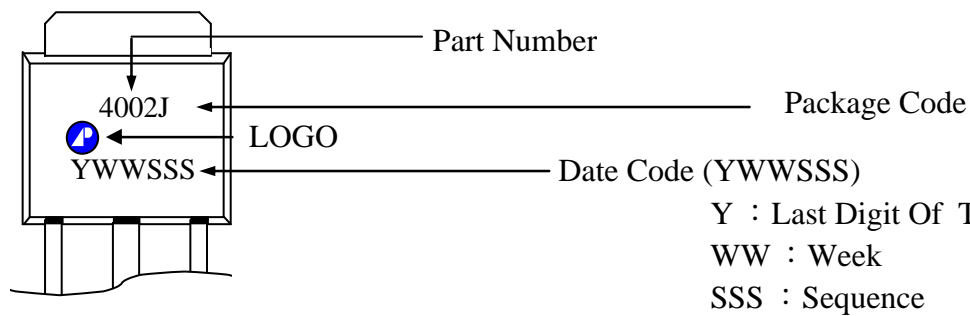
4002H
 YWWSSS
 Y : Last Digit Of The Year
 WW : Week
 SSS : Sequence



SYMBOLS	Millimeters		
	MIN	NOM	MAX
	Original	Original	Original
A	2.10	2.30	2.50
A1	0.60	1.20	1.80
B1	0.40	0.60	0.80
B2	0.60	0.95	1.25
c	0.40	0.50	0.65
c1	0.40	0.55	0.70
D	6.00	6.50	7.00
D1	4.80	5.40	5.90
E1	5.00	5.50	6.00
E2	1.20	1.70	2.20
e	----	2.30	----
F	7.00	---	16.70

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.

Part Marking Information & Packing : TO-251



Y : Last Digit Of The Year
 WW : Week
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